

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki et al. Art Unit : 2871
Serial No. : 09/809,646 Examiner : Thoi V. Duong
Filed : March 16, 2001 Conf. No. : 5011
Title : SEMICONDUCTOR DISPLAY DEVICE AND MANUFACTURING METHOD
THEREOF

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR INITIALED PTO FORM 1449

Upon reviewing the file, applicants noted that they have not received an initialed copy of the enclosed PTO Form 1449 that accompanied a supplemental information disclosure statement filed December 29, 2006.

Applicants' records show that this information disclosure statement complied with 37 CFR 1.97. Thus, it is respectfully requested that the examiner initial and return this form as soon as possible. Note, applicants are paying the issue fee and publication fee concurrently herewith, so the examiner's prompt attention to this matter would be appreciated.

Respectfully submitted,

Date: February 27, 2007



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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-021001	Application No. 09/809,646
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Shunpei Yamazaki	
		Filing Date March 16, 2001	Group Art Unit 2871

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
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	AB	2002-0142512	10/03/2002	Ma			03/29/2001
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Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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Foreign Patent Documents or Published Foreign Patent Applications								
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							Yes	No
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							Yes	No
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	CD	

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